



STB80NF55L-06

N - CHANNEL 55V - 0.005 Ω - 80A D²PAK STripFET™ POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STB80NF55L-06	55 V	< 0.0065 Ω	80 A

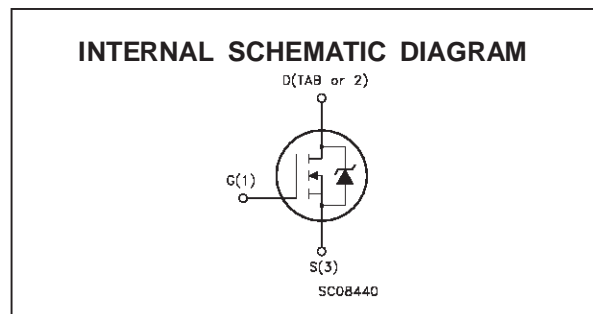
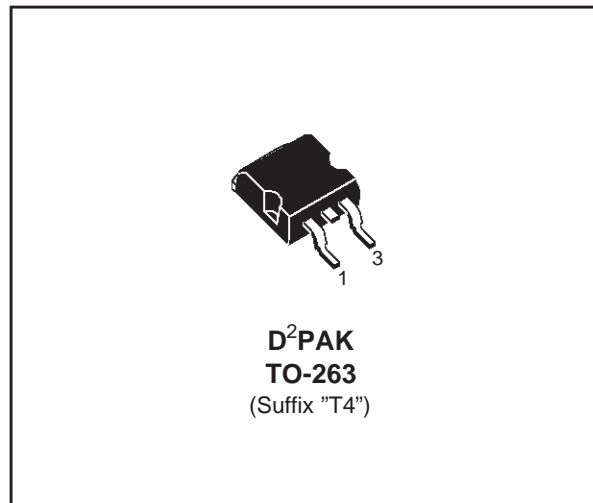
- TYPICAL R_{DS(on)} = 0.005 Ω
- LOW THRESHOLD DRIVE
- LOGIC LEVEL DEVICE
- ADD SUFFIX "T4" FOR ORDERING IN TAPE & REEL

DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC & DC-AC CONVERTERS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	55	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	55	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	80	A
I _D	Drain Current (continuous) at T _c = 100 °C	57	A
I _{DM} (●)	Drain Current (pulsed)	320	A
P _{tot}	Total Dissipation at T _c = 25 °C	210	W
	Derating Factor	1.4	W/°C
E _{AS} (1)	Single Pulse Avalanche Energy	1	J
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(●) Pulse width limited by safe operating area

(1) starting T_j = 25 °C, I_D = 40A, V_{DD} = 30V

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THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	0.71	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	62.5	$^{\circ}C/W$
T_l	Maximum Lead Temperature For Soldering Purpose		300	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu A$ $V_{GS} = 0$	55			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_c = 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20 V$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu A$	1	1.6	2.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10 V$ $I_D = 40 A$ $V_{GS} = 5 V$ $I_D = 40 A$		0.005 0.0055	0.0065 0.008	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10 V$	80			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 18 A$		20		S
C_{iss}	Input Capacitance	$V_{DS} = 25 V$ $f = 1 MHz$ $V_{GS} = 0$		7600		pF
C_{oss}	Output Capacitance			990		pF
C_{rss}	Reverse Transfer Capacitance			270		pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 27\text{ V}$ $I_D = 40\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, see fig. 3)		75		ns
t_r	Rise Time			300		ns
Q_g	Total Gate Charge	$V_{DD} = 44\text{ V}$ $I_D = 80\text{ A}$ $V_{GS} = 5\text{ V}$		97	100	nC
Q_{gs}	Gate-Source Charge			25		nC
Q_{gd}	Gate-Drain Charge			46		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off Delay Time	$V_{DD} = 27\text{ V}$ $I_D = 40\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, see fig. 3)		210		ns
t_f	Fall Time			160		ns
$t_{d(off)}$	Off-voltage Rise Time	$V_{clamp} = 44\text{ V}$ $I_D = 80\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Inductive Load, see fig. 5)		90		ns
t_f	Fall Time			230		ns
t_c	Cross-over Time			350		ns

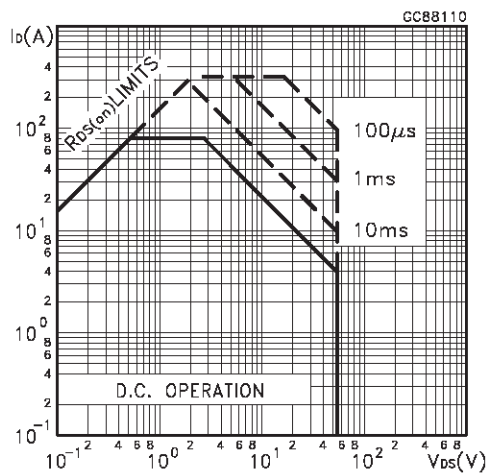
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				80	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				320	A
$V_{SD}(\ast)$	Forward On Voltage	$I_{SD} = 80\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 80\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 25\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, fig. 5)		75		ns
Q_{rr}	Reverse Recovery Charge			190		nC
I_{RRM}	Reverse Recovery Current			5.1		A

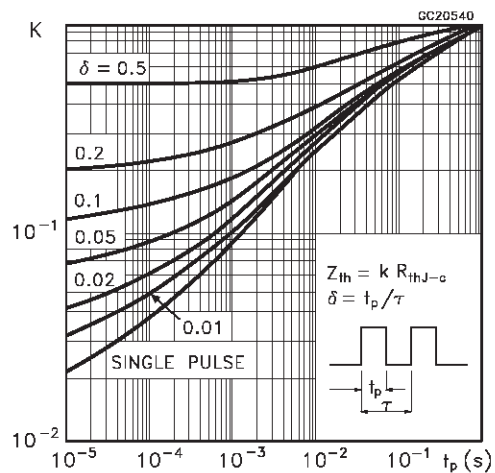
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

(•) Pulse width limited by safe operating area

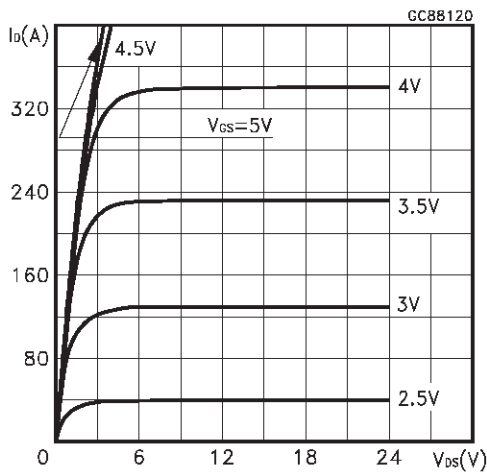
Safe Operating Area



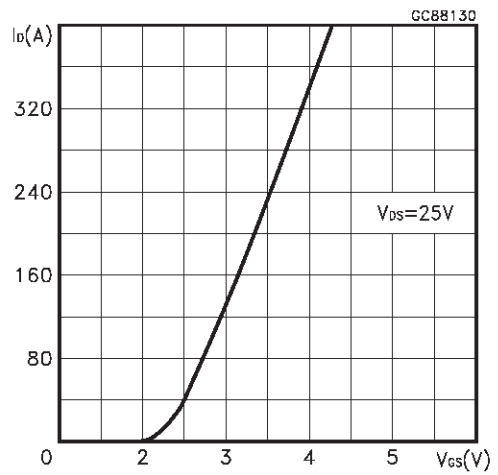
Thermal Impedance



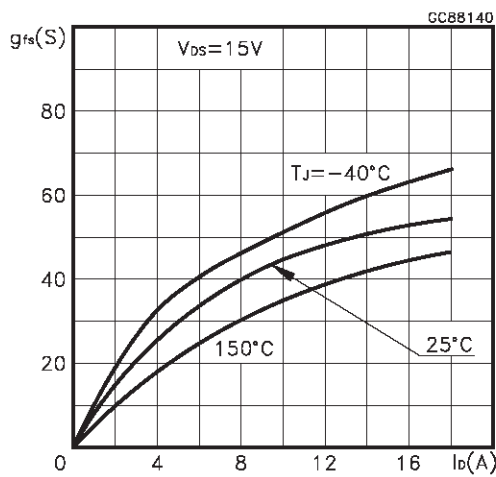
Output Characteristics



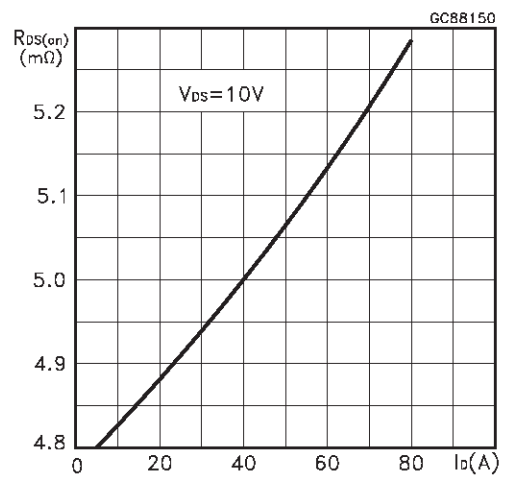
Transfer Characteristics



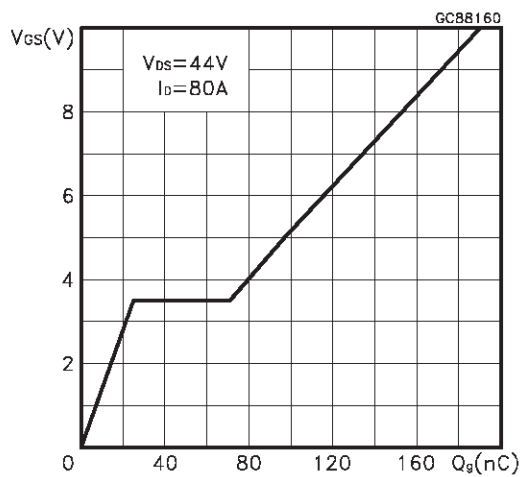
Transconductance



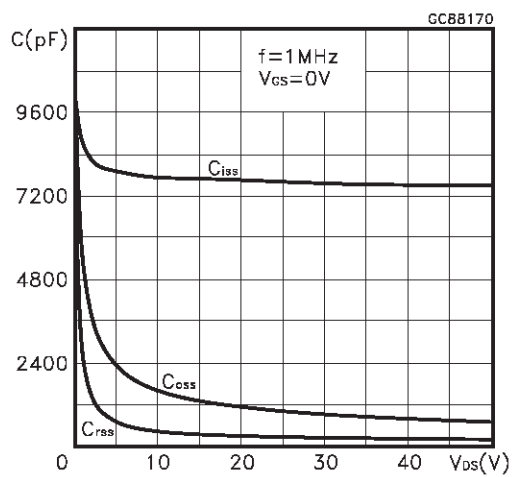
Static Drain-source On Resistance



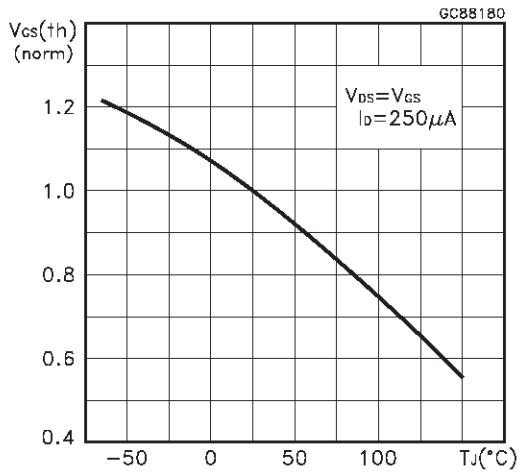
Gate Charge vs Gate-source Voltage



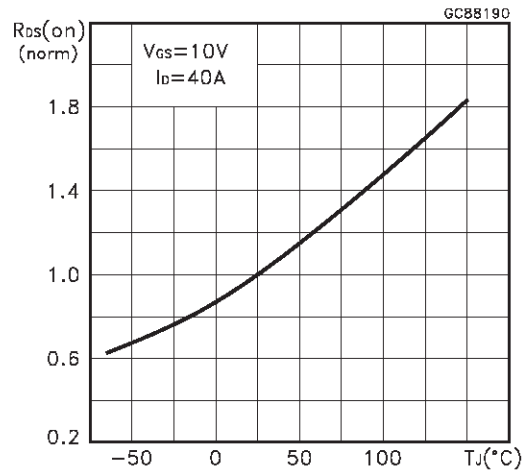
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

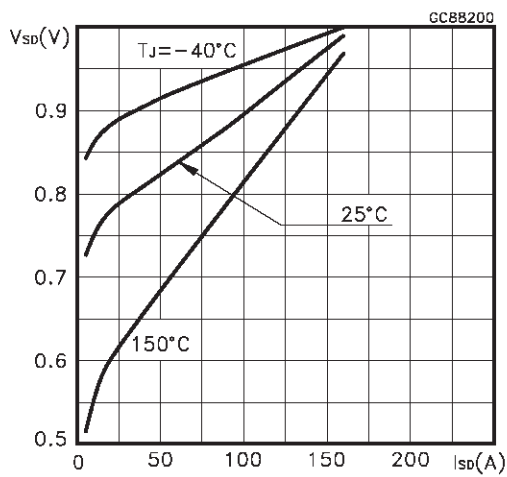


Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform



Fig. 3: Switching Times Test Circuits For Resistive Load



Fig. 4: Gate Charge test Circuit

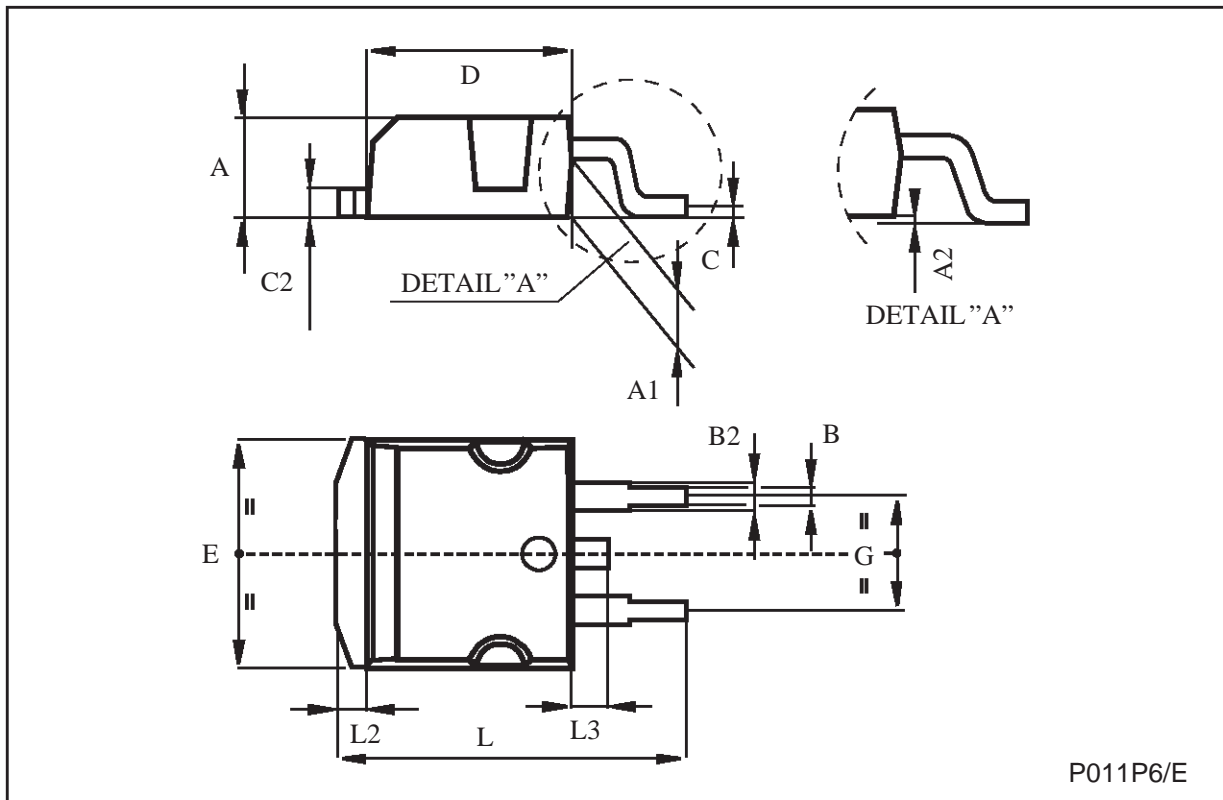


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-263 (D²PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.21		1.36	0.047		0.053
D	8.95		9.35	0.352		0.368
E	10		10.4	0.393		0.409
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068



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